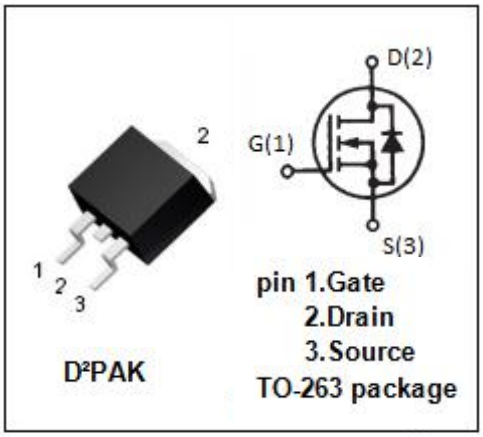
isc N-Channel MOSFET Transistor TK16G60W

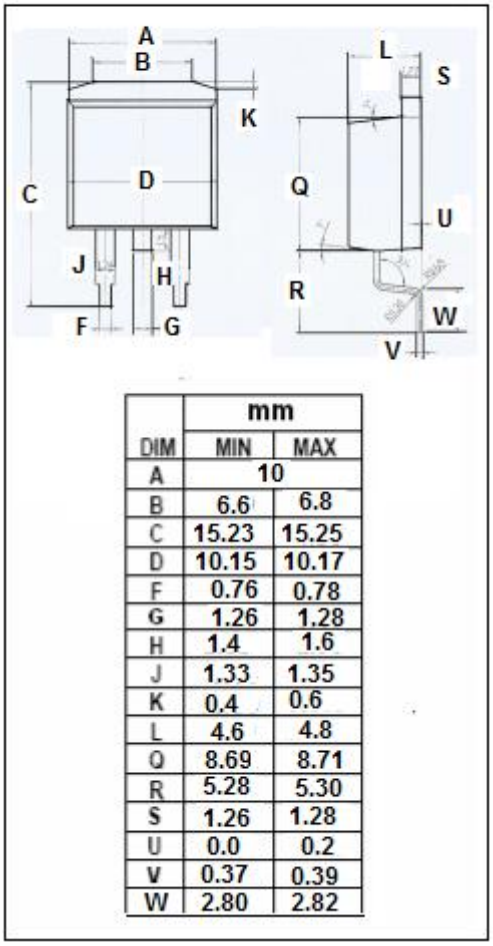
- **FEATURES**
- Low drain-source on-resistance:
  R_{DS}(on) ≤0.19Ω.
- Enhancement mode:
  Vth =2.7 to 3.7V (V_{DS} = 10 V, I_D=0.79mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



- **DESCRITION**
- Switching Voltage Regulators

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Drain Current-Continuous	15.8	A
I_{DM}	Drain Current-Single Pulsed	63.2	A
P_D	Total Dissipation @T_C=25℃	130	W
T_j	Max. Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃



DIM	mm MIN	MAX
A	10	
B	6.6	6.8
C	15.23	15.25
D	10.15	10.17
F	0.76	0.78
G	1.26	1.28
H	1.4	1.6
J	1.33	1.35
K	0.4	0.6
L	4.6	4.8
Q	8.69	8.71
R	5.28	5.30
S	1.26	1.28
U	0.0	0.2
V	0.37	0.39
W	2.80	2.82

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.962	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D=10mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=10V; I_D=0.79mA	2.7		3.7	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}=10V; I_D=7.9A			0.19	Ω
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±30V;V_{DS}= 0V			±1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}=600V; V_{GS}= 0V			10	μA
V_{SDF}	Diode forward voltage	I_{DR} =15.8A, V_{GS} = 0 V			1.7	V